

FQPF50N06L

60V LOGIC N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

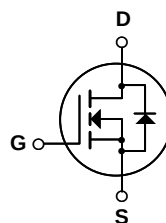
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as automotive, DC/DC converters, and high efficiency switching for power management in portable and battery operated products.

Features

- 32.6A, 60V, $R_{DS(on)} = 0.021\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 24.5 nC)
- Low C_{rss} (typical 90 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



TO-220F
FQPF Series



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQPF50N06L	Units
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	32.6	A
		23.1	A
I_{DM}	Drain Current - Pulsed (Note 1)	130	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1000	mJ
I_{AR}	Avalanche Current (Note 1)	32.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	4.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	47	W
		0.31	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	3.22	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.06	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 48\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 16.3\text{ A}$	--	0.017	0.021	Ω
		$V_{GS} = 5\text{ V}, I_D = 16.3\text{ A}$	--	0.020	0.025	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 25\text{ V}, I_D = 16.3\text{ A}$ (Note 4)	--	35	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1250	1630	pF
C_{oss}	Output Capacitance		--	445	580	pF
C_{rss}	Reverse Transfer Capacitance		--	90	120	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 26.2\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	20	50	ns
t_r	Turn-On Rise Time		--	380	770	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	170	ns
t_f	Turn-Off Fall Time		--	145	300	ns
Q_g	Total Gate Charge	$V_{DS} = 48\text{ V}, I_D = 52.4\text{ A},$ $V_{GS} = 5\text{ V}$ (Note 4, 5)	--	24.5	32	nC
Q_{gs}	Gate-Source Charge		--	6	--	nC
Q_{gd}	Gate-Drain Charge		--	14.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	32.6	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	130	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 32.6 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 52.4 A,	--	65	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	125	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 1.1\text{ mH}, I_{AS} = 32.6\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 52.4\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

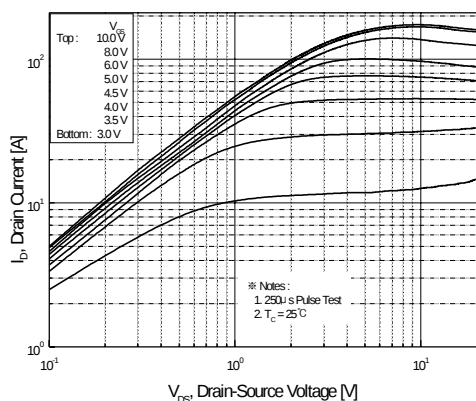


Figure 1. On-Region Characteristics

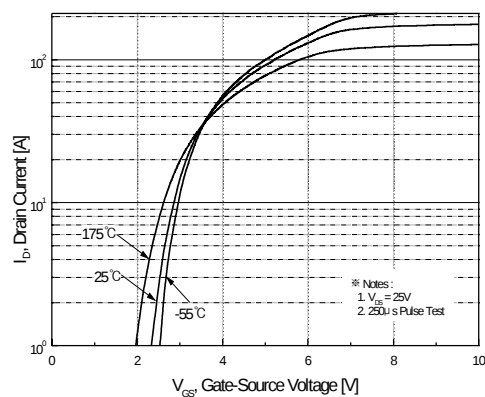


Figure 2. Transfer Characteristics

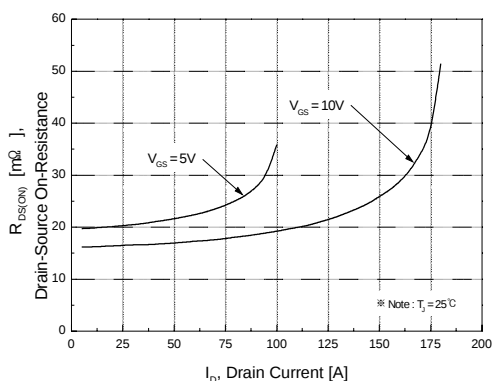


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

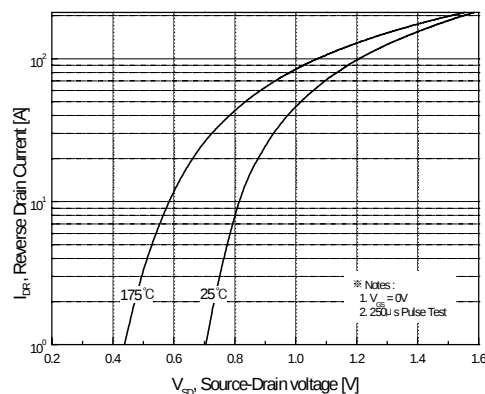


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

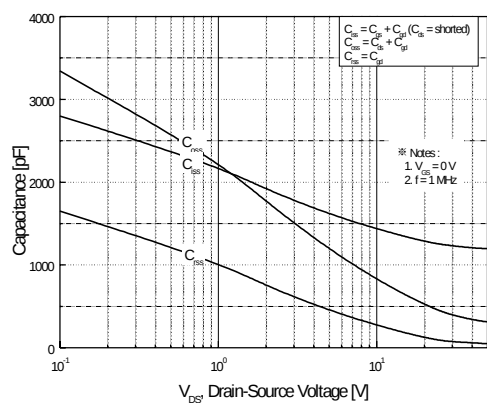


Figure 5. Capacitance Characteristics

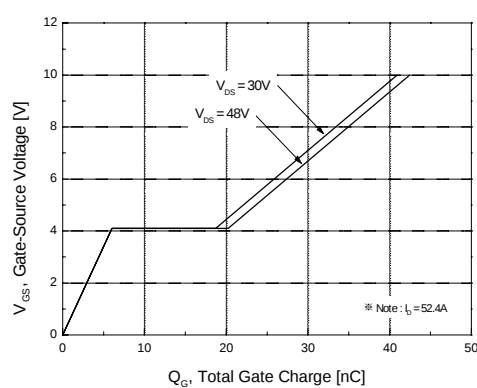


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

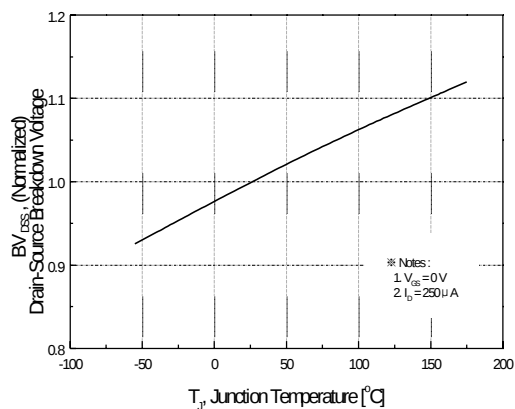


Figure 7. Breakdown Voltage Variation vs. Temperature

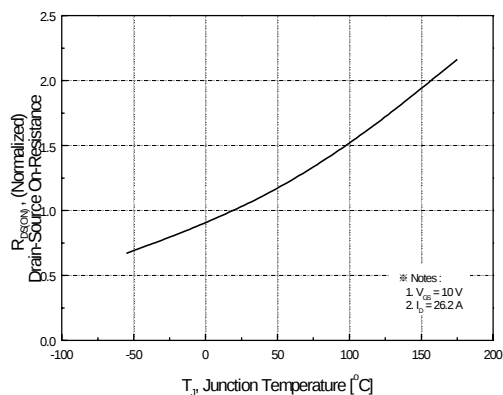


Figure 8. On-Resistance Variation vs. Temperature

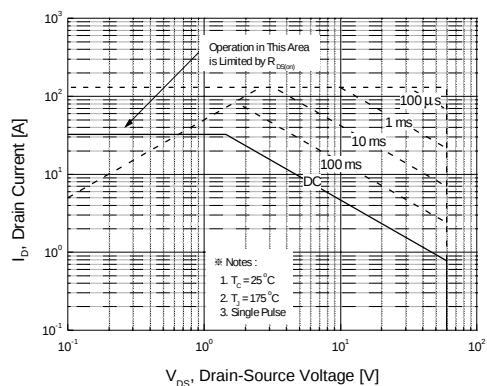


Figure 9. Maximum Safe Operating Area

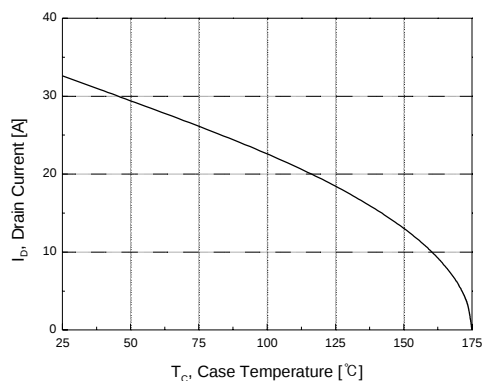


Figure 10. Maximum Drain Current vs. Case Temperature

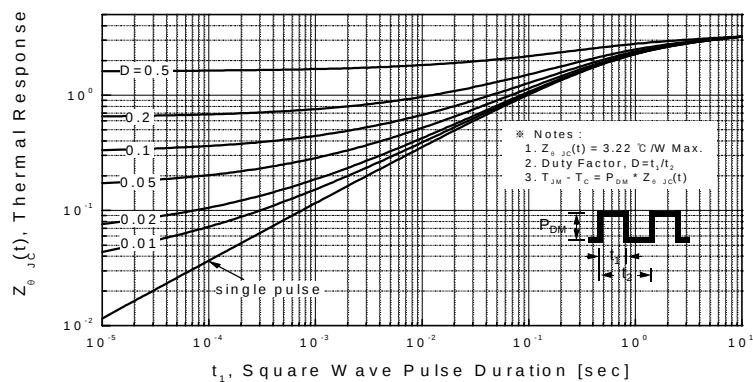
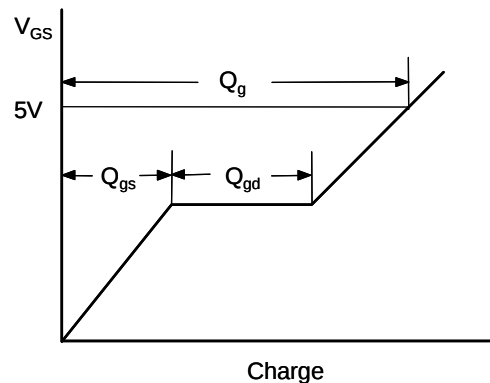
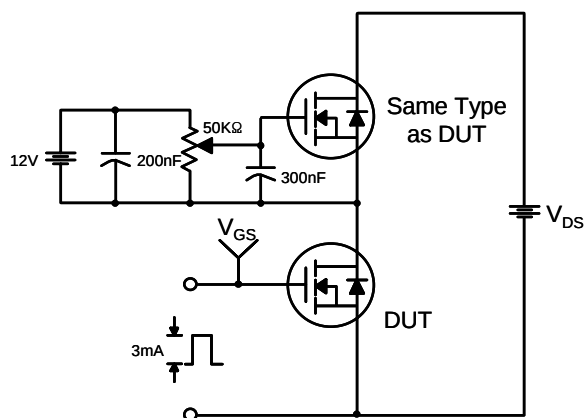
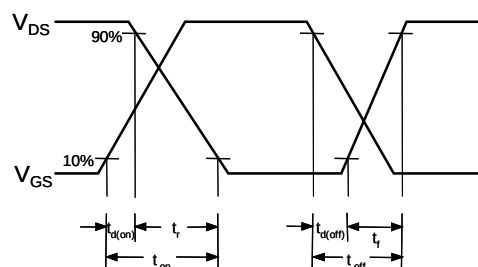
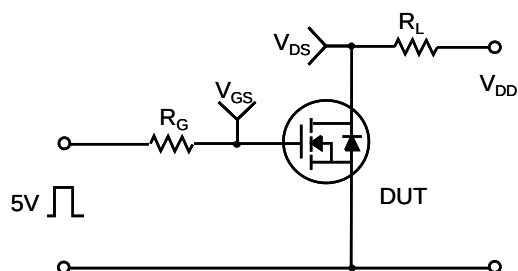


Figure 11. Transient Thermal Response Curve

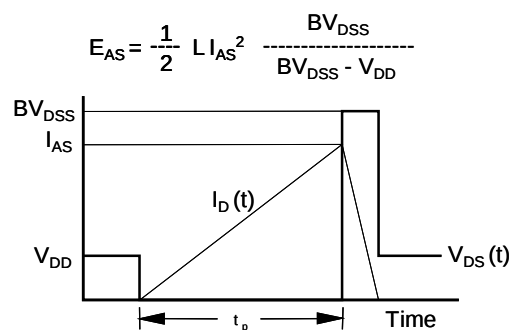
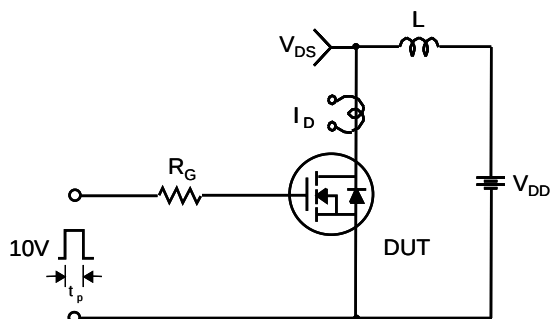
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



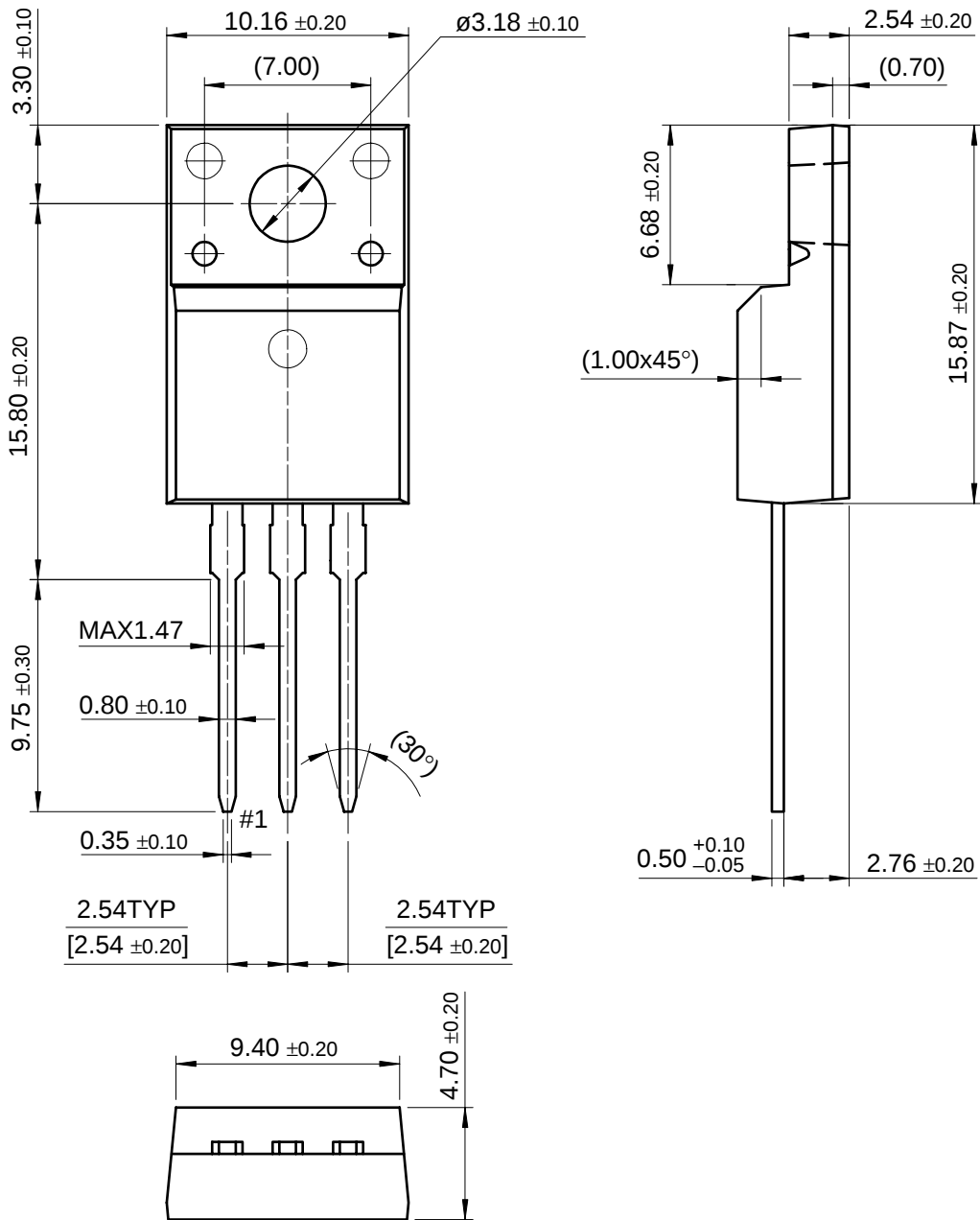
The top diagram shows a circuit for testing the body diode of a MOSFET. The DUT (Device Under Test) is a MOSFET with its gate connected to its drain. The source is connected to the source of a driver MOSFET. The driver's gate is driven by a square wave V_{GS} through a resistor R_G . The driver's drain is connected to the DUT's drain through an inductor L . The DUT's source is connected to ground. The DUT's drain-source voltage is V_{DS} , and the source-drain current is I_{SD} . The driver is of the same type as the DUT. The supply voltage is V_{DD} .

Below the circuit, three waveforms are shown:

- V_{GS} (Driver):** A square wave pulse. The duty cycle is defined as $D = \frac{\text{Gate Pulse Width}}{\text{Gate Pulse Period}}$. The pulse height is 10V.
- I_{SD} (DUT):** The source-drain current. It shows a forward current I_{FM} during the pulse, followed by a reverse current I_{RM} during the recovery phase. The recovery phase is labeled di/dt .
- V_{DS} (DUT):** The drain-source voltage. It shows a forward voltage drop V_{SD} during the pulse, followed by a recovery phase labeled $Body Diode Recovery dv/dt$. The reverse voltage is V_{DD} .

Package Dimensions

TO-220F



FQPF50N06L

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